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Dae Gyu PARK

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INFORMATION DISCLOSURE STATEMENT

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U.S. PATENT DOCUMENTS

*Examiner Initials	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

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						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

~	C1	Park, Dae-Gyu, et al., "Properties of reactive-sputtered $Ti_{1-x}Al_xN$ thin films", Meeting Abstracts of The 195 th Meeting of The Electrochemical Society, Inc. in Seattle, Washington on May 2-6, 1999, Abstract No. 476
~	C2	Moriwaki, M., et al., "Impacts of Chlorine in CVD-TiN Gate Electrode on the Gate Oxide Reliability in Multiple-Thickness Oxide Technology", Extended Abstracts of the 2000 International Conference on Solid State Devices and Materials, Sendai, 2000, pp. 188-189
~	C3	Hu, J.C., et al., "Feasibility of Using W/TiN as Metal Gate for Conventional 0.13 μm CMOS Technology and Beyond", International Electron Devices Meeting (IEDM 97) pp. 825-828, ©1997 IEEE
~	C4	Nakajima, K., et al., "Work Function Controller Metal Gate Electrode on Ultrathin Gate Insulators", 1999 Symposium on VLSI Technology Digest of Technical Papers, pp. 95-96
~	C5	Amazawa, T., et al., "Surface State Generation of Mo Gate Metal Oxide Semiconductor Devices Caused by Mo Penetration into Gate Oxide", J. Electrochem. Soc., Vol. 145, No. 4, April 1998 © The Electrochemical Society, Inc.

EXAMINER

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